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The invention is intended to enhance the precision of pattern inspection of a reflection type photomask used in EUV lithography by observing reflectivity contrast of DUV light. In a reflection type photomask blank having a multilayer reflection film (2) and a light absorption laminated layer (4) laminated on a substrate (1), the light absorption laminated layer (4) is composed by laminating a second light absorption layer (42) having DUV light absorbing capacity and containing at least one of nitrogen and oxygen, and tantalum and silicon, on a first light absorption layer (41) having EUV light absorbing capacity and containing tantalum and silicon.